



DUAL 30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UXC)

Product Summary

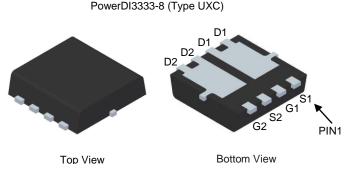
BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C			
30V	$10m\Omega @ V_{GS} = 10V$	25A			
307	14mΩ @ V _{GS} = 4.5V	20A			

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

Applications

- Power Management Functions
- Analog Switch

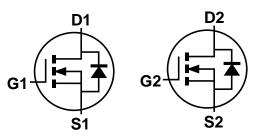


Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]3333-8 (Type UXC)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (€3)
- Weight: 0.072 grams (Approximate)



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3006LDV-7	PowerDI3333-8 (Type UXC)	2000/Tape & Reel
DMT3006LDV-13	PowerDI3333-8 (Type UXC)	3000/Tape & Reel

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

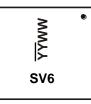
3.Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, see https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:

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 $\frac{SV6}{YY}WW = Date Code Marking Code$ $\frac{YY}{YY} = Last Two Digits of Year (ex: 18 for 2018)$ WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 7)	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	Ι _D	25 20	A
Maximum Body Diode Forward Current (Note 7)		ls	25	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	90	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	90	A
Avalanche Current (L = 0.1mH) (Note 8)			I _{AS}	34	A
Avalanche Energy (L = 0.1mH) (Note 8)			E _{AS}	58	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)	PD	0.9	W		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	134	°C/W	
mermai Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\Theta JA}$	78	0/00	
Total Power Dissipation (Note 6)		PD	1.8	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	70		
t<10s		R _{ƏJA}	41	°C/W	
Thermal Resistance, Junction to Case (Note 7)	R _{eJC}	14			
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			-				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)			1	1	r		
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	$V_{GS} = +20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			7.6	10	mΩ	V _{GS} = 10V, I _D = 9.0A	
	R _{DS(ON)}	_	10.0	14		V _{GS} = 4.5V, I _D = 8.5A	
Diode Forward Voltage	V _{SD}	_	0.70	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	1,155	_		$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Output Capacitance	Coss	_	456	_	pF		
Reverse Transfer Capacitance	Crss	_	72	_			
Gate Resistance	R _G	_	1.6	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	8.4	—			
Total Gate Charge (V _{GS} = 10V)	Q _G	_	16.7	_	nC		
Gate-Source Charge	Q _{GS}	_	2.2	_	nc	$V_{DD} = 15V, I_D = 9A$	
Gate-Drain Charge	Q _{GD}	_	3.5	_			
Turn-On Delay Time	t _{D(ON)}	_	3.5	_		V_{DD} = 15V, V_{GS} = 10V, R _G = 3Ω, I _D = 9A	
Turn-On Rise Time	t _R	_	5.5	_			
Turn-Off Delay Time	t _{D(OFF)}	_	13.5	_	ns		
Turn-Off Fall Time	tF	—	4.6	_	1		
Reverse Recovery Time	t _{RR}	_	19.3	_	ns		
Reverse Recovery Charge	Q _{RR}	_	8.6	_	nC	I _F = 1.5A, di/dt = 100A/μs	

5. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided. Notes:

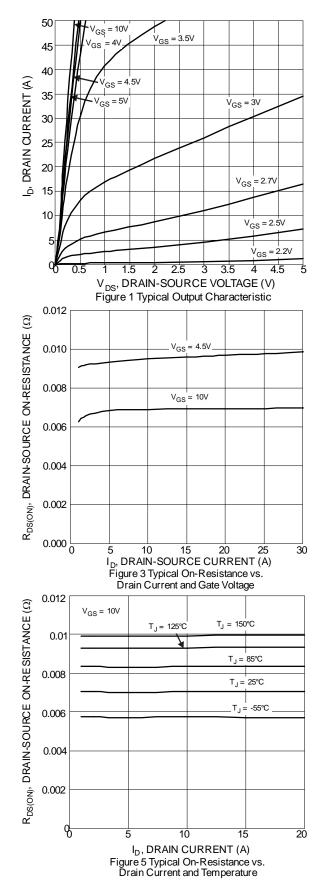
Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).

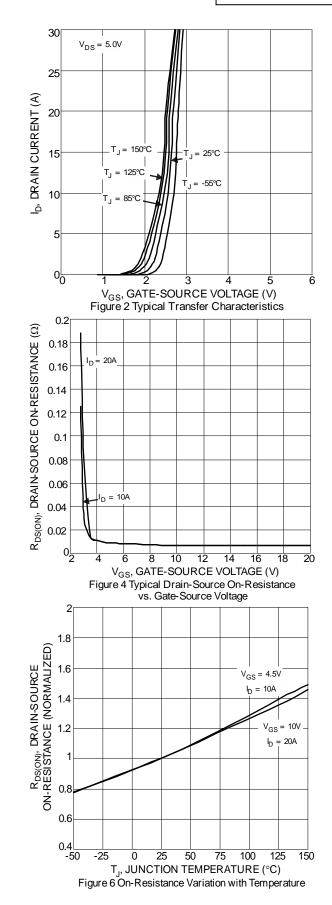
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

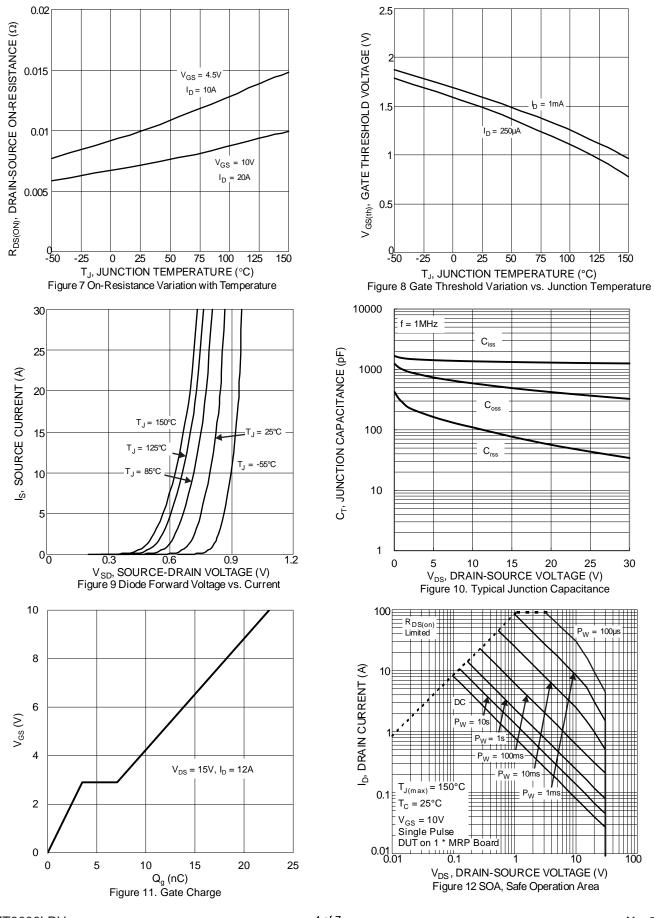






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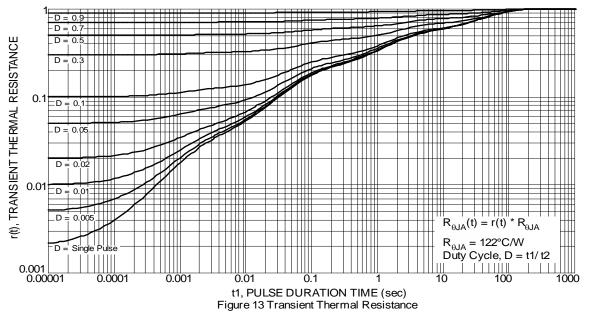




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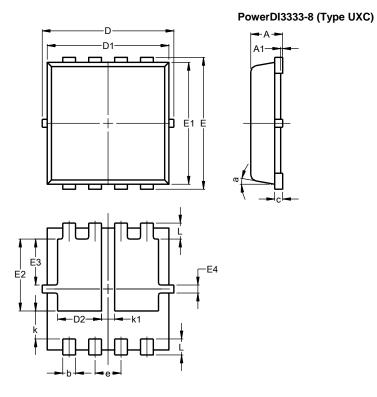
DMT3006LDV





Package Outline Dimensions

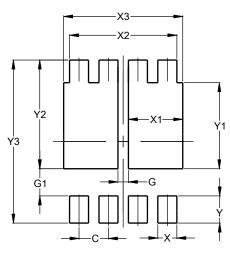
Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI3333-8						
	(Type UXC)					
Dim	Min Max		Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	_			
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	0.90	1.30	1.10			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_		0.65			
L	0.30	0.50	0.40			
k	0.50	0.90	0.70			
k1	0.13	0.53	0.33			
а	0°	12°	10°			
All D	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI3333-8 (Type UXC)

Dimensions	Value (in mm)		
С	0.650		
G	0.230		
G1	0.600		
Х	0.420		
X1	1.200		
X2	2.370		
X3	2.630		
Y	0.600		
Y1	1.900		
Y2	2.400		
Y3	3.600		



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